COMPLETE LISTING OF CLAIMS

IN ASCENDING ORDER WITH STATUS INDICATOR

1 (Currently amended). A method of producing a complex oxide thin-film comprising the steps of:

(a) providing a metal compound solution comprising at least two metal compounds dissolved in a solvent;

(b) atomizing the metal compound solution in a two-fluid nozzle having a discharge end in a film-forming chamber, and directly introducing the atomized solution into the film-forming chamber in which the pressure is about 100 Torr or lower and having a substrate therein by mixing a gas with the metal compound solution in the two-fluid nozzle and discharging the atomized mixture into the chamber, and

(c) forming a complex oxide thin-film on a substrate in the film-forming chamber at a temperature equal to or higher than the boiling point of the solvent.

2 (Original). A method of producing a complex oxide thin-film according to claim 1, wherein the solution is atomized in the two-fluid nozzle with an oxidative gas.

3 (Original). A method of producing a complex oxide thin-film according to claim 2, wherein the solvent has a boiling point of at least 100° C under ordinary pressure.

4 (Original). A method of producing a complex oxide thin-film according to claim 3, wherein at least one of the metal compounds is a dipivaloylmethanato complex.

5 (Original). A method of producing a complex oxide thin-film according to claim 4, wherein at least one of the metal compounds is an acetylacetonato complex.

C1 cont'd

6 (Original). A method of producing a complex oxide thin-film according to claim 5, wherein the solution contains three metal compounds and at least one of the metal compounds is a metal alkoxide.

7 (Original). A method of producing a complex oxide thin-film according to claim 6, wherein the film-forming (c) is performed at least two times, and after each film-forming, the film is heat-treated under a pressure lower than that employed for the film forming.

8 (Original). A method of producing a complex oxide thin-film according to claim 7, wherein at least the film obtained after the final-forming is heat treated at an oxygen gas partial pressure higher than an oxygen gas partial pressure existent during film-forming.

9 (Original). A method of producing a complex oxide thin-film according to claim 1, wherein the solvent has a boiling point of at least about 100° C under ordinary pressure.

10 (Original). A method of producing a complex oxide thin-film according to claim 1, wherein at least one of the metal compounds is a dipivaloylmethanato complex.

11 (Original). A method of producing a complex oxide thin-film according to claim 1, wherein at least one of the metal compounds is an acetylacetonato complex.

12 (Original). A method of producing a complex oxide thin-film according to claim 1, wherein at least one of the metal compounds is a metal alkoxide.

C1 cont'd

13 (Original). A method of producing a complex oxide thin-film according to claim 1, wherein the film-forming is performed at least two times, and after each film-forming, the film is heat-treated under a pressure lower than that employed for the film-forming.

14 (Original). A method of producing a complex oxide thin-film according to claim 1, wherein at least the film obtained by the final film-forming is heat treated at an oxygen gas partial pressure higher than an oxygen gas partial pressure existent during film-forming.

15-18 (CANCELLED).